1SS383T1G, 1SS383T2G

Preferred Device

Dual Schottky Diode

Dual 40 V, 300 mA Low V_F Schottky Diodes in 4−lead SC−82 package.

Features

- Low Forward Voltage: V_F = 0.48 V (typ) @ I_F = 100 mA
- Low Reverse Current: I_R = 5 μA (max)
- Pb−Free Package May be Available. The G−Suffix Denotes a Pb−Free Lead Finish

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Continuous Reverse Voltage	V_R	40	V
Maximum Peak Forward Current*	I_{FM}	300	mA
Peak Forward Surge Current Pulse Width = 10 μs	$I_{FM(surge)}$	500	mA

*Both Devices Active

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit

THERMAL CHARACTERISTICS

Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D	200 (Note 1) 1.6 (Note 1)	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	625 (Note 1)	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

1. FR−4 @ Minimum Pad.

ELECTRICAL CHARACTERISTICS
(T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Forward Voltage (I_F = 1.0 mA) (I_F = 10 mA) (I_F = 100 mA)	V_F	 – – –	 280 360 540	 – – 600	mV
Reverse Current (V_R = 40 V)	I_R	–	–	5	μA
Capacitance (V_R = 0, f = 1.0 MHz)	C_D	–	–	25	pF

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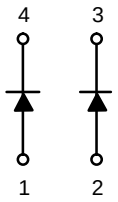


SC−82
CASE 900AA

MARKING DIAGRAM

AE = Specific Device Code
D = Date Code

ORDERING INFORMATION

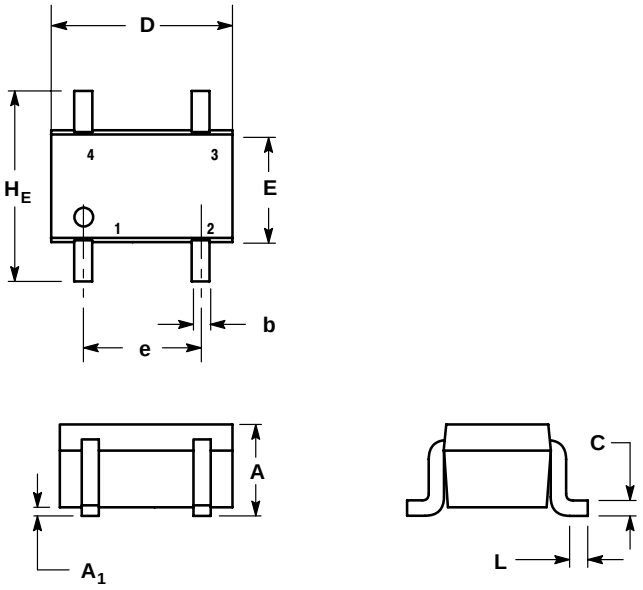
Device	Package	Shipping†
1SS383T1G	SC−82	4 mm pitch 3000/Tape & Reel
1SS383T2G	SC−82	4 mm pitch 3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

PACKAGE DIMENSIONS

SC−82, 4 LEAD, GULL WING
CASE 900AA−01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUMTHICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.04
A_1	0	−−−	0.10	0	−−−	0.004
b	0.10	0.20	0.30	0.004	0.008	0.012
C	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.15	1.25	1.35	0.045	0.049	0.053
e	1.30 BSC			0.051 BSC		
H_E	2.00	2.10	2.20	0.079	0.083	0.087
L	0.10	0.20	0.30	0.004	0.008	0.012

STYLE 1:
PIN 1. ANODE 1
2. ANODE 2
3. CATHODE 2
4. CATHODE 1

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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